

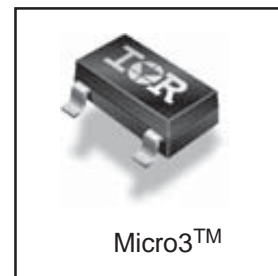
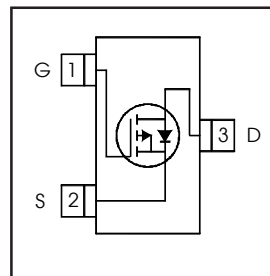
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge

V <sub>DSS</sub>	R <sub>DS(on)</sub> max (mΩ)	I <sub>D</sub>
<b>-30V</b>	98@V <sub>GS</sub> = -10V	-3.0A
	165@V <sub>GS</sub> = -4.5V	-2.6A

### Description

These P-channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



### Absolute Maximum Ratings

	Parameter	Max.	Units
V <sub>DS</sub>	Drain- Source Voltage	-30	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-3.0	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ -10V	-2.4	
I <sub>DM</sub>	Pulsed Drain Current ①	-24	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation	1.25	W
P <sub>D</sub> @ T <sub>A</sub> = 70°C	Power Dissipation	0.80	
	Linear Derating Factor	10	mW/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 150	°C

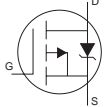
### Thermal Resistance

	Parameter	Max.	Units
R <sub>θJA</sub>	Maximum Junction-to-Ambient③	100	°C/W

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	98	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.0A ②
		—	—	165		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.6A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	-1.0	—	-2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	3.1	—	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.0A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
		—	—	-5.0		V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 20V
Q <sub>g</sub>	Total Gate Charge	—	9.5	14	nC	I <sub>D</sub> = -3.0A
Q <sub>gs</sub>	Gate-to-Source Charge	—	2.3	3.5		V <sub>DS</sub> = -24V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	1.6	2.4		V <sub>GS</sub> = -10V ②
t <sub>d(on)</sub>	Turn-On Delay Time	—	12	—	ns	V <sub>DD</sub> = -15V ②
t <sub>r</sub>	Rise Time	—	18	—		I <sub>D</sub> = -1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	88	—		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	52	—		V <sub>GS</sub> = -10V
C <sub>iss</sub>	Input Capacitance	—	510	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	71	—		V <sub>DS</sub> = -25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	43	—		f = 1.0MHz

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-24		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -1.3A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	17	26	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -1.3A
Q <sub>rr</sub>	Reverse Recovery Charge	—	12	18	nC	di/dt = -100A/μs ②

### Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400μs; duty cycle ≤ 2%.

③ Surface mounted on FR-4 board, t ≤ 5sec.

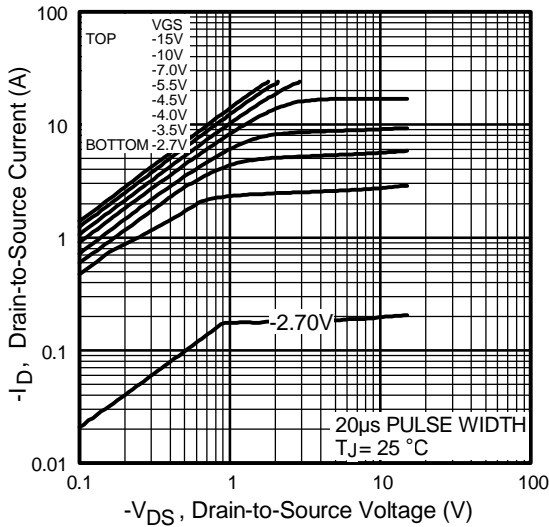


Fig 1. Typical Output Characteristics

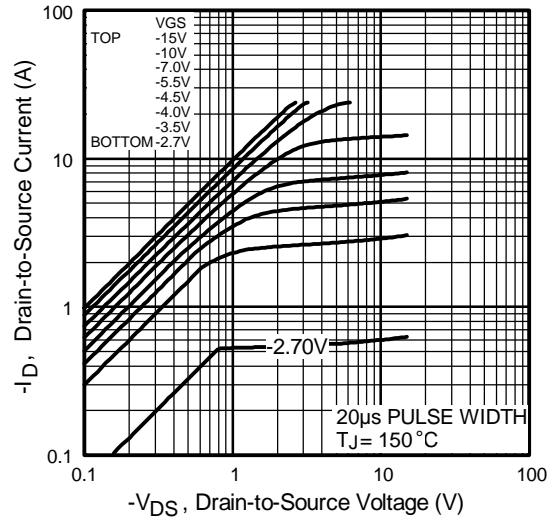


Fig 2. Typical Output Characteristics

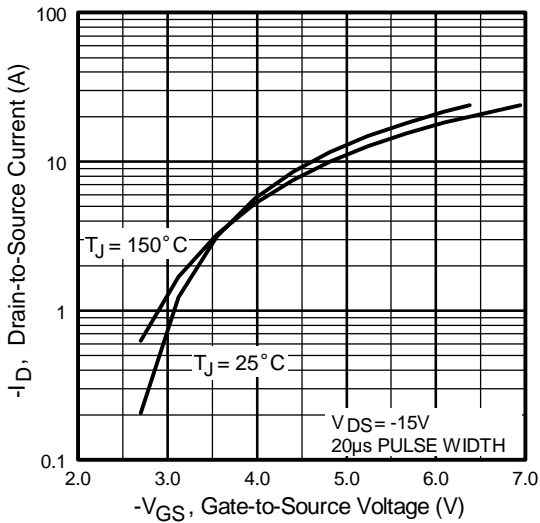


Fig 3. Typical Transfer Characteristics

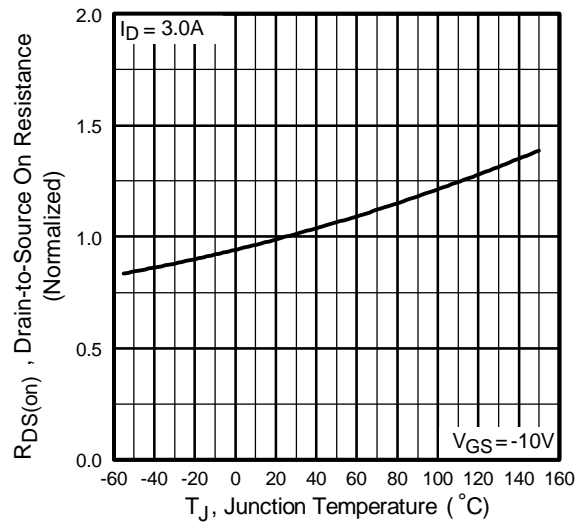
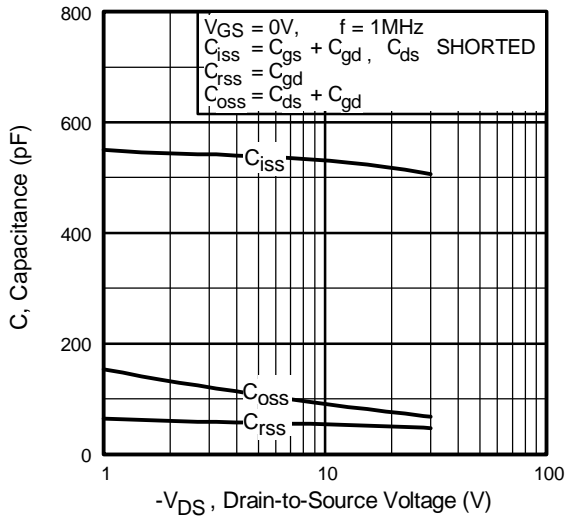
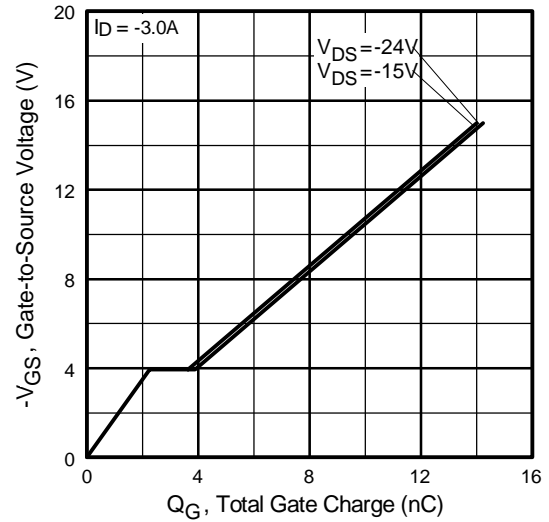


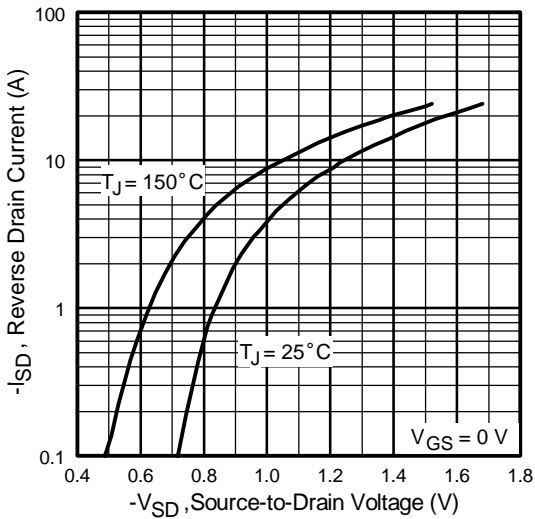
Fig 4. Normalized On-Resistance Vs. Temperature



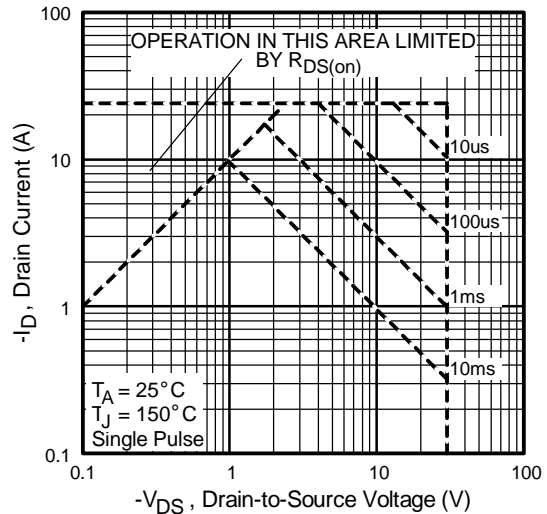
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

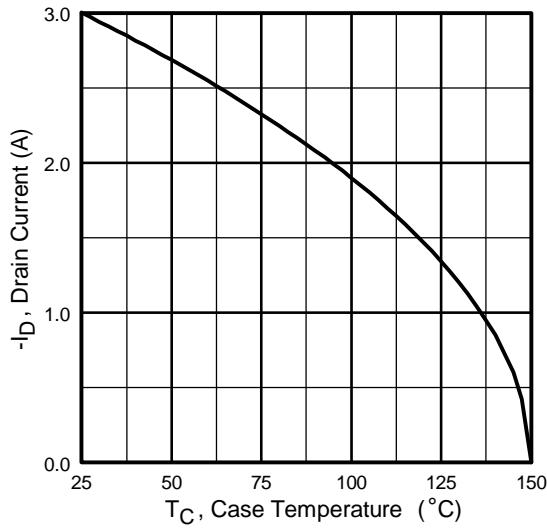


Fig 9. Maximum Drain Current Vs. Case Temperature

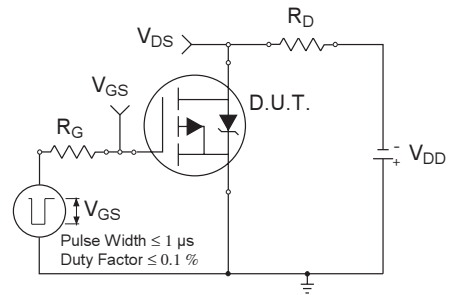


Fig 10a. Switching Time Test Circuit

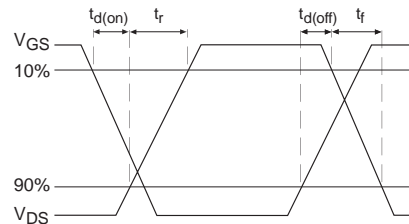


Fig 10b. Switching Time Waveforms

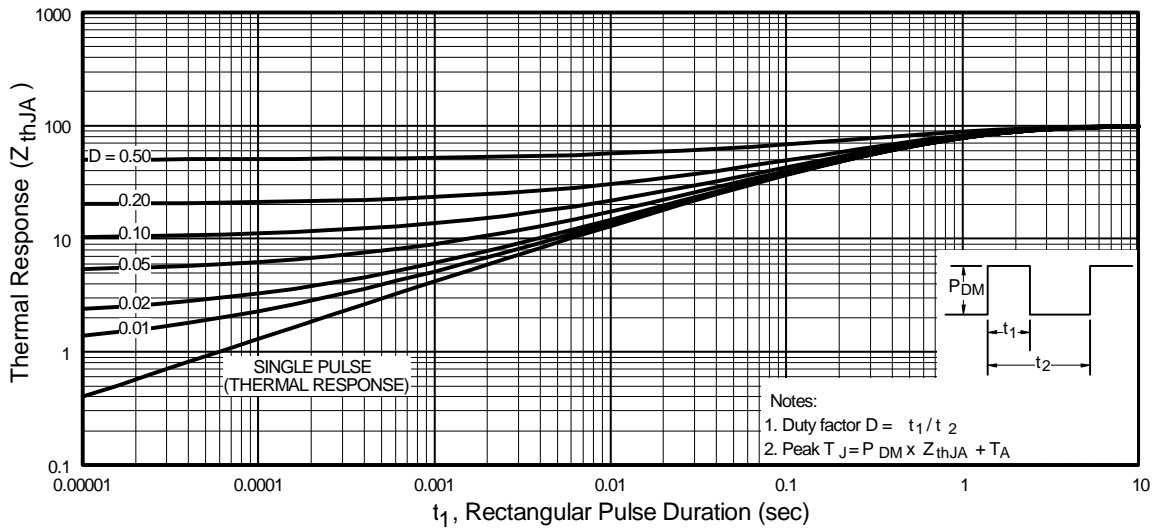
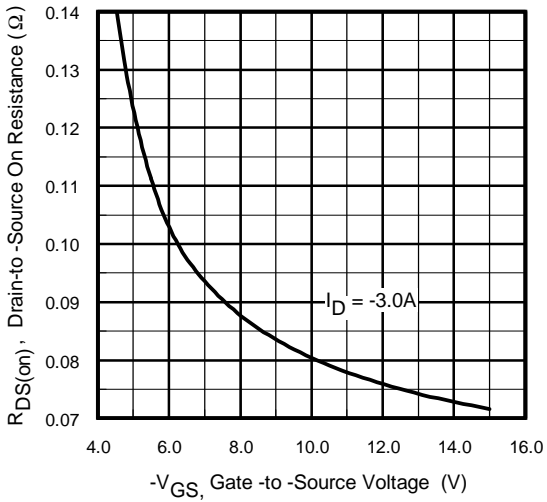
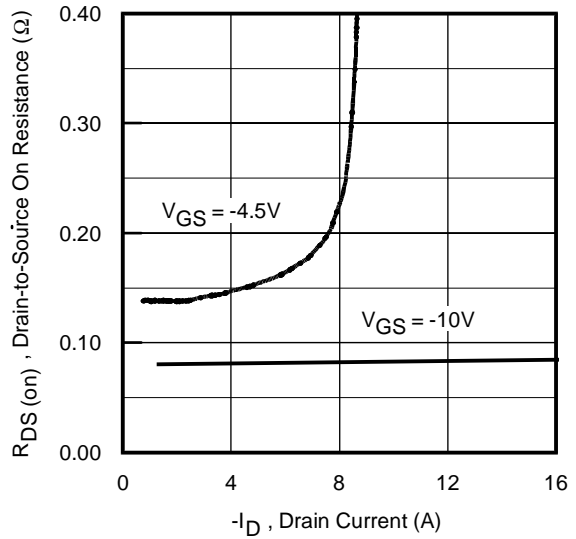


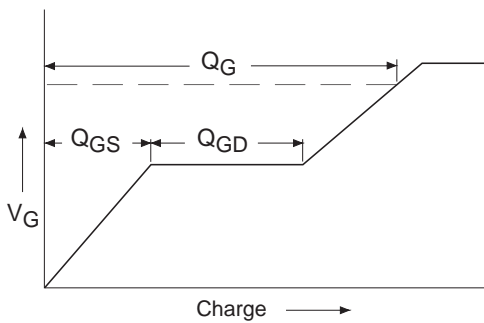
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



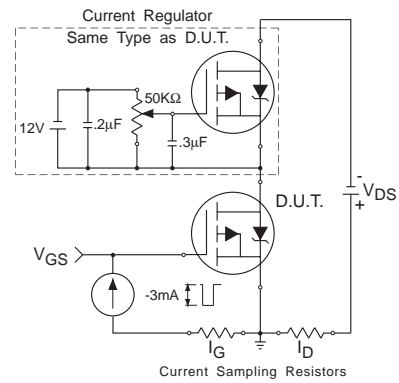
**Fig 11.** Typical On-Resistance Vs. Gate Voltage



**Fig 12.** Typical On-Resistance Vs. Drain Current



**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

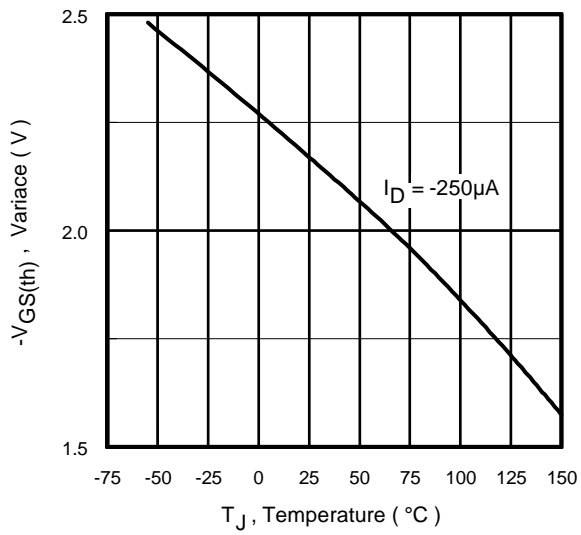


Fig 14. Threshold Voltage Vs. Temperature

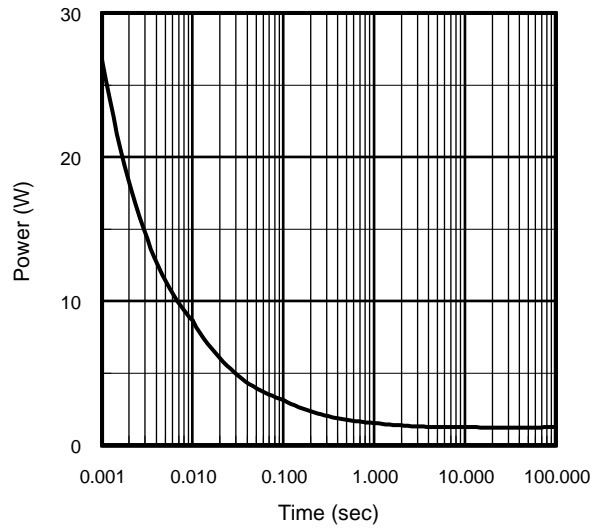
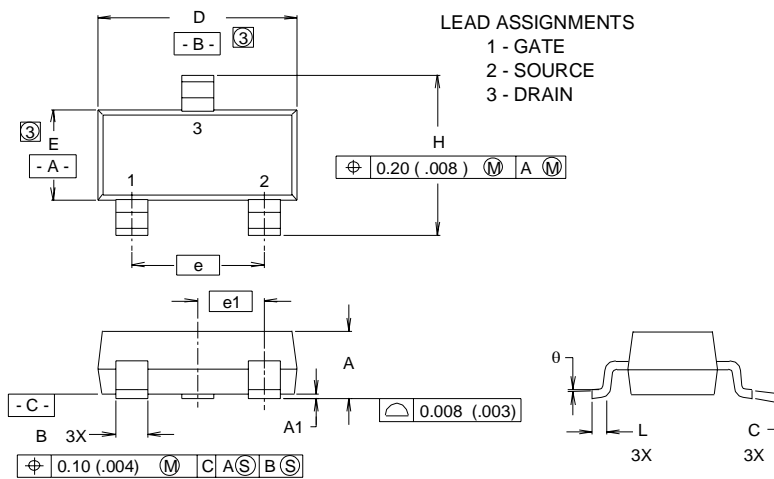


Fig 15. Typical Power Vs. Time

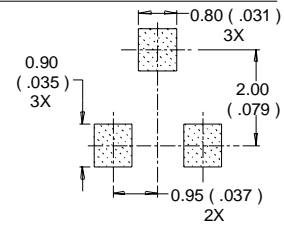
## Micro3™ Package Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.032	.044	0.82	1.11
A1	.001	.004	0.02	0.10
B	.015	.021	0.38	0.54
C	.004	.006	0.10	0.15
D	.105	.120	2.67	3.05
e	.0750 BASIC		1.90 BASIC	
e1	.0375 BASIC		0.95 BASIC	
E	.047	.055	1.20	1.40
H	.083	.098	2.10	2.50
L	.005	.010	0.13	0.25
θ	0°	8°	0°	8°

### MINIMUM RECOMMENDED FOOTPRINT



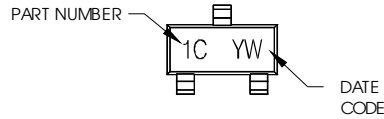
- NOTES:  
 1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.  
 2. CONTROLLING DIMENSION : INCH.  
 ③ DIMENSIONS DO NOT INCLUDE MOLD FLASH.



Notes: This part marking information applies to devices produced before 02/26/2001

EXAMPLE: THIS IS AN IRLML6302

WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- 1A = IRLML2402
- 1B = IRLML2803
- 1C = IRLML6302
- 1D = IRLML5103
- 1E = IRLML6402
- 1F = IRLML6401
- 1G = IRLML2502
- 1H = IRLML5203

DATE CODE EXAMPLES:

- YWW = 9503 = 5C
- YWW = 9532 = EF

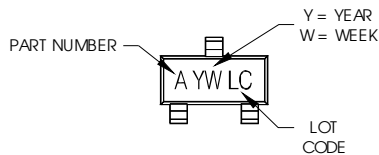
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2001	1	01	A
2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Notes: This part marking information applies to devices produced after 02/26/2001

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- A = IRLML2402
- B = IRLML2803
- C = IRLML6302
- D = IRLML5103
- E = IRLML6402
- F = IRLML6401
- G = IRLML2502
- H = IRLML5203

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

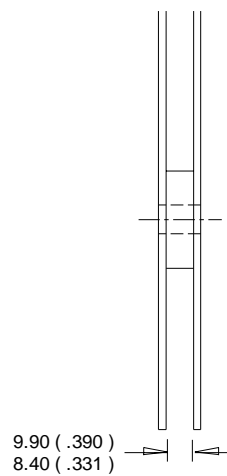
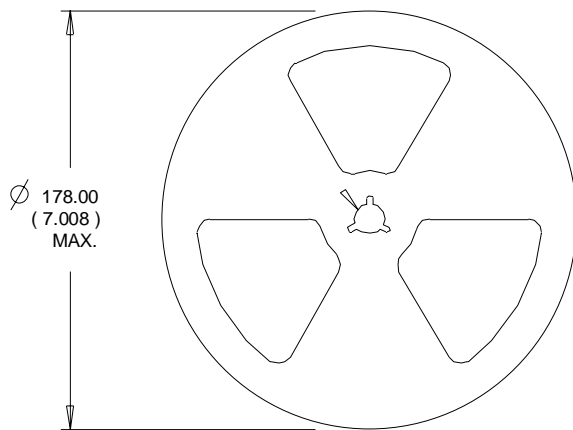
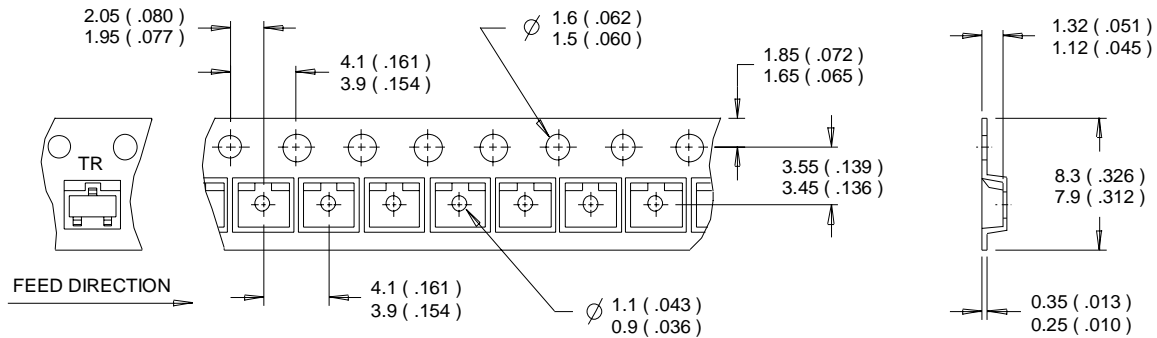
# IRLML5203

PROVISIONAL

International  
**IOR** Rectifier

## Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



### NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.

International  
**IOR** Rectifier

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